

Power MOSFET



FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- For automatic insertion
- End stackable
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

PRODUCT SUMMARY

| | | |
|---------------------------|------------------------|-----|
| V_{DS} (V) | 250 | |
| $R_{DS(on)}$ (Ω) | $V_{GS} = 10\text{ V}$ | 2.0 |
| Q_g (Max.) (nC) | 8.2 | |
| Q_{gs} (nC) | 1.8 | |
| Q_{gd} (nC) | 4.5 | |
| Configuration | Single | |

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The 4 pin DIP package is a low cost machine-insertable case style which can be stacked in multiple combinations on standard 0.1" pin centers. The dual drain serves as a thermal link to the mounting surface for power dissipation levels up to 1 W.

ORDERING INFORMATION

| | |
|----------------|------------|
| Package | HVMDIP |
| Lead (Pb)-free | IRFD214PbF |

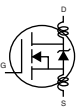

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT |
|--|----------------|-----------------------------------|---------------------|
| Drain-source voltage | V_{DS} | 250 | V |
| Gate-source voltage | V_{GS} | ± 20 | |
| Continuous drain current | I_D | $T_A = 25\text{ }^\circ\text{C}$ | A |
| | | $T_A = 100\text{ }^\circ\text{C}$ | |
| Pulsed drain current ^a | I_{DM} | 3.6 | |
| Linear derating factor | | 0.0083 | W/ $^\circ\text{C}$ |
| Single pulse avalanche energy ^b | E_{AS} | 57 | mJ |
| Repetitive avalanche current ^a | I_{AR} | 0.45 | A |
| Repetitive avalanche energy ^a | E_{AR} | 0.10 | mJ |
| Maximum power dissipation | P_D | 1.0 | W |
| Peak diode recovery dV/dt ^c | dV/dt | 4.8 | V/ns |
| Operating junction and storage temperature range | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |
| Soldering recommendations (peak temperature) | For 10 s | 300 ^d | |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^\circ\text{C}$, $L = 28\text{ mH}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 1.8\text{ A}$ (see fig. 12)
- $I_{SD} \leq 2.7\text{ A}$, $dI/dt \leq 65\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$
- 1.6 mm from case

| THERMAL RESISTANCE RATINGS | | | | |
|-----------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient | R_{thJA} | - | 120 | °C/W |

| SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted) | | | | | | | |
|--|---------------------|--|--|------|------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | | 250 | - | - | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to 25 °C , $I_D = 1\text{ mA}$ | | - | 0.39 | - | V/°C |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | | 2.0 | - | 4.0 | V |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$ | | - | - | 25 | μA |
| | | $V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ °C}$ | | - | - | 250 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 0.27\text{ A}^b$ | - | - | 2.0 | Ω |
| Forward Transconductance | g_{fs} | $V_{DS} = 50\text{ V}, I_D = 1.6\text{ A}$ | | 0.90 | - | - | S |
| Dynamic | | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz}$, see fig. 5 | | - | 140 | - | μF |
| Output Capacitance | C_{oss} | | | - | 42 | - | |
| Reverse Transfer Capacitance | C_{rss} | | | - | 9.6 | - | |
| Total Gate Charge | Q_g | $V_{GS} = 10\text{ V}$ | $I_D = 2.7\text{ A}, V_{DS} = 200\text{ V},$ see fig. 6 and 13 ^b | - | - | 8.2 | nC |
| Gate-Source Charge | Q_{gs} | | | - | - | 1.8 | |
| Gate-Drain Charge | Q_{gd} | | | - | - | 4.5 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 125\text{ V}, I_D = 2.7\text{ A},$ $R_g = 24\text{ }\Omega, R_D = 45\text{ }\Omega$, see fig. 10 ^b | | - | 7.0 | - | ns |
| Rise Time | t_r | | | - | 7.6 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | - | 16 | - | |
| Fall Time | t_f | | | - | 7.0 | - | |
| Internal Drain Inductance | L_D | Between lead, 6 mm (0.25") from package and center of die contact  | | - | 4.0 | - | nH |
| Internal Source Inductance | L_S | | | - | 6.0 | - | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous Source-Drain Diode Current | I_S | MOSFET symbol showing the integral reverse p - n junction diode  | | - | - | 0.45 | A |
| Pulsed Diode Forward Current ^a | I_{SM} | | | - | - | 3.6 | |
| Body Diode Voltage | V_{SD} | $T_J = 25\text{ °C}, I_S = 0.45\text{ A}, V_{GS} = 0\text{ V}^b$ | | - | - | 2.0 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $T_J = 25\text{ °C}, I_F = 9.2\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$ | | - | 190 | 390 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | - | 0.64 | 1.3 | μC |
| Forward Turn-On Time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D) | | | | | |

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
 b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

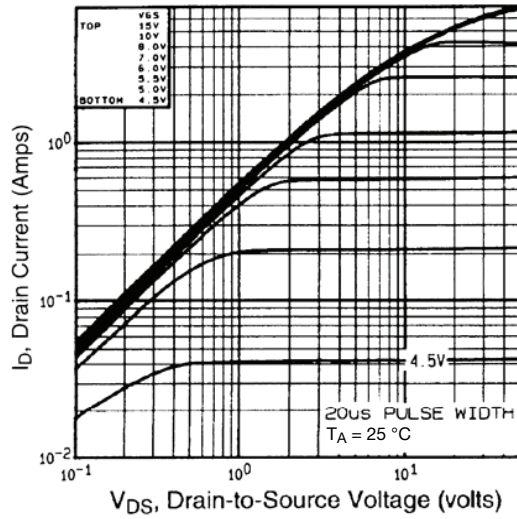


Fig. 1 - Typical Output Characteristics, $T_A = 25\text{ °C}$

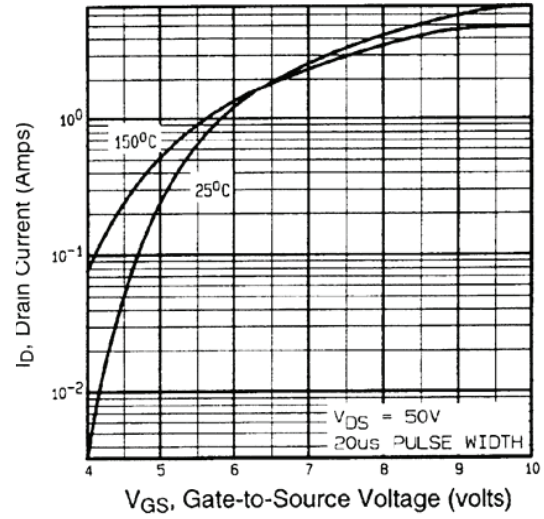


Fig. 2 - Typical Transfer Characteristics

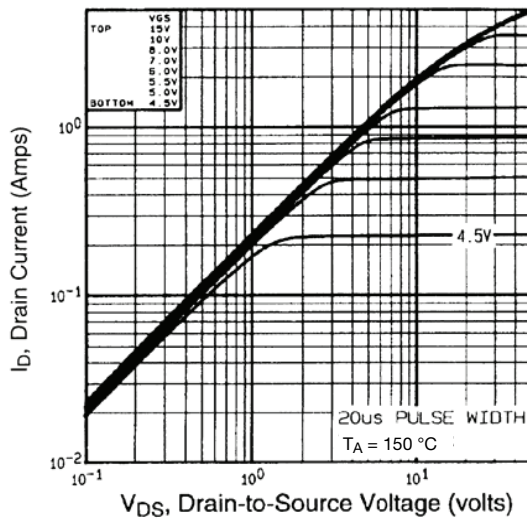


Fig. 1 - Typical Output Characteristics, $T_A = 150\text{ °C}$

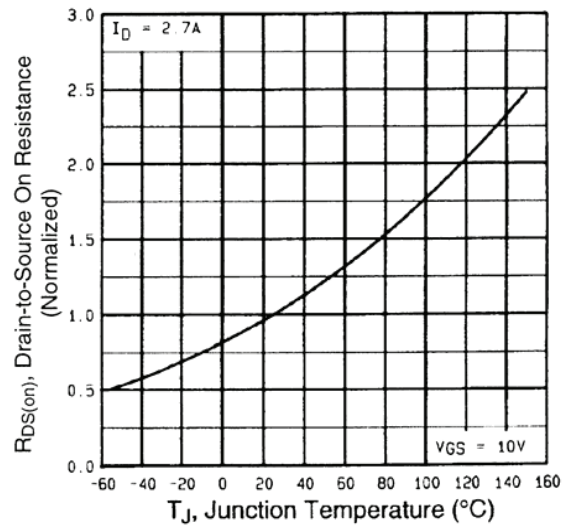


Fig. 3 - Normalized On-Resistance vs. Temperature

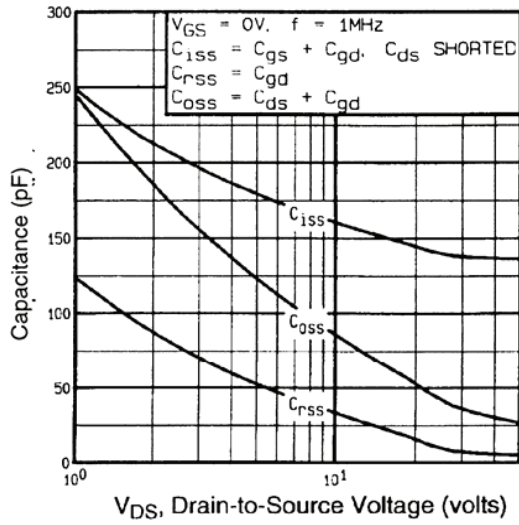


Fig. 4 - Typical Capacitance vs. Drain-to-Source Voltage

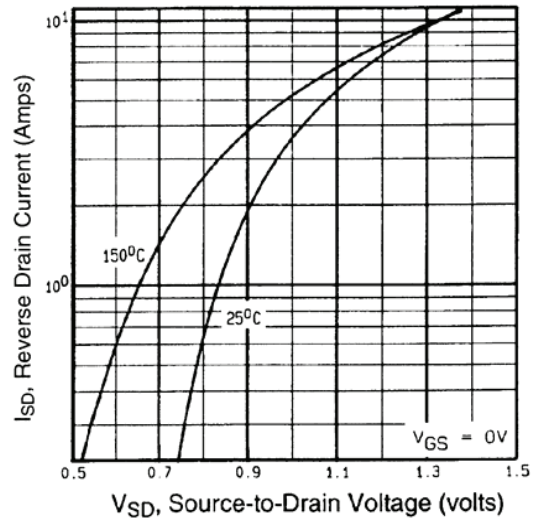


Fig. 6 - Typical Source-Drain Diode Forward Voltage

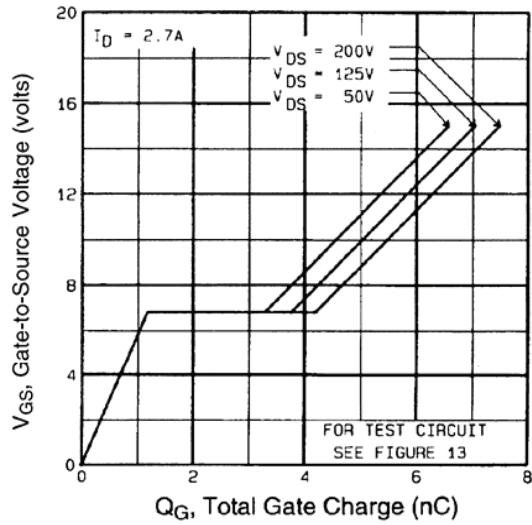


Fig. 5 - Typical Gate Charge vs. Gate-to-Source Voltage

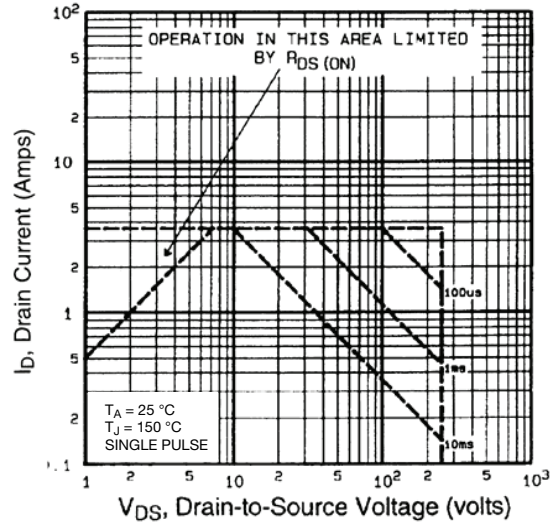


Fig. 7 - Maximum Safe Operating Area

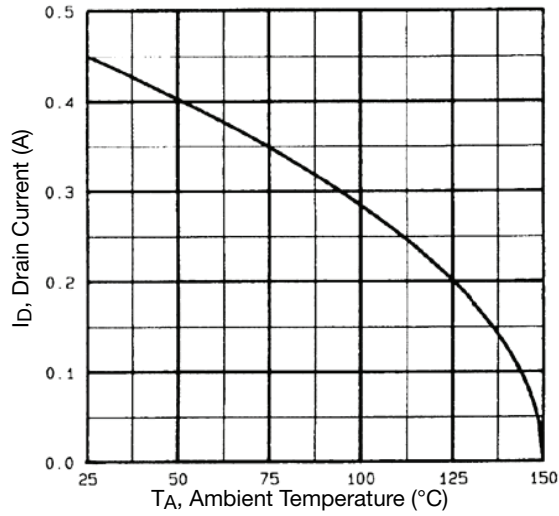


Fig. 8 - Maximum Drain Current vs. Ambient Temperature



Fig. 10a - Switching Time Test Circuit

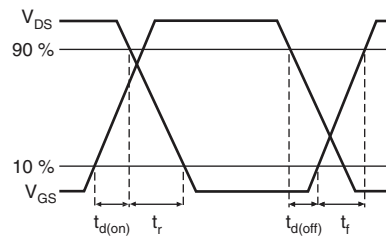


Fig. 10b - Switching Time Waveforms

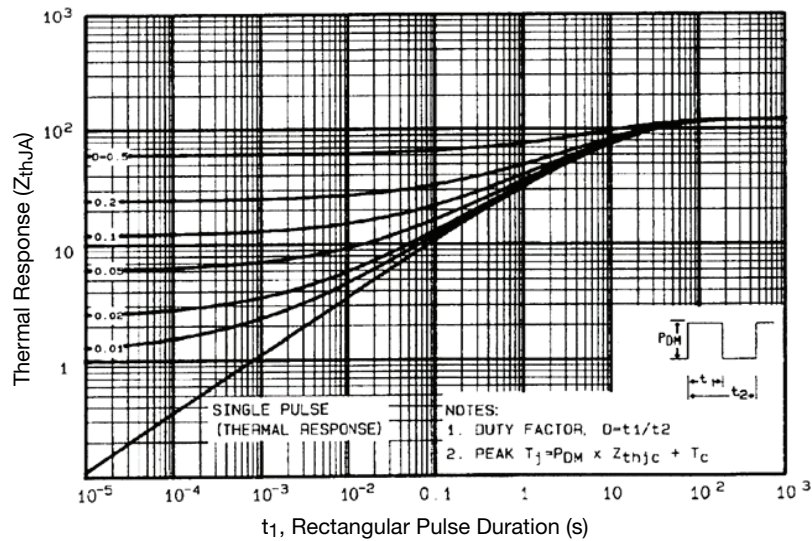


Fig. 9 - Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Fig. 12a - Unclamped Inductive Test Circuit

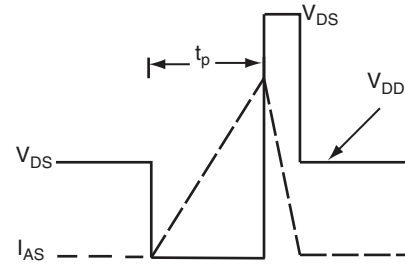


Fig. 12b - Unclamped Inductive Waveforms

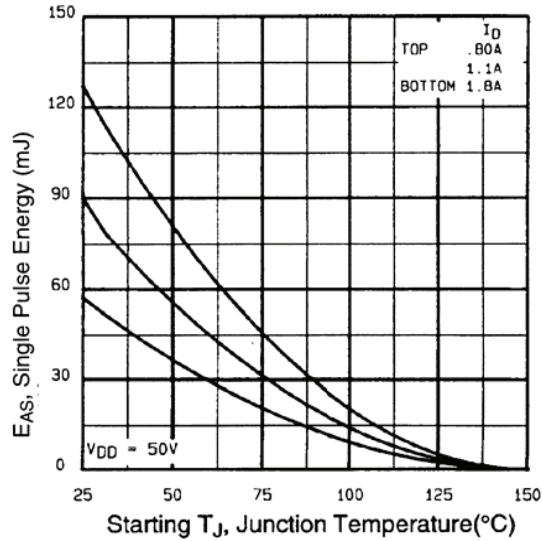


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

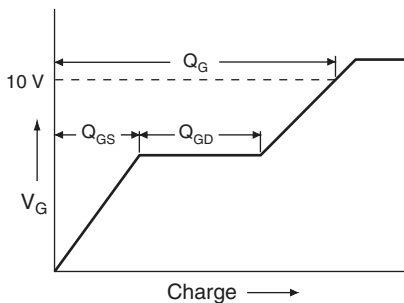


Fig. 13a - Basic Gate Charge Waveform

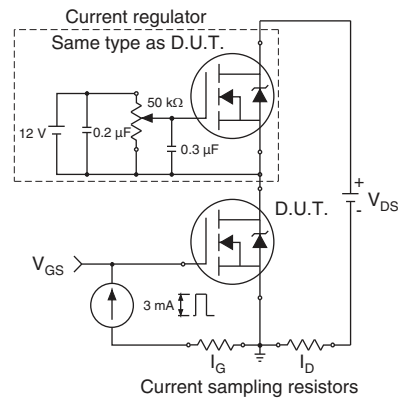


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 10 - For N-Channel

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HVM DIP (High voltage)



| DIM. | INCHES | | MILLIMETERS | |
|------|--------|-------|-------------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 0.310 | 0.330 | 7.87 | 8.38 |
| E | 0.300 | 0.425 | 7.62 | 10.79 |
| L | 0.270 | 0.290 | 6.86 | 7.36 |

ECN: X10-0386-Rev. B, 06-Sep-10
DWG: 5974

Note

- Package length does not include mold flash, protrusions or gate burrs. Package width does not include interlead flash or protrusions.



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